

Product Summary

Device	BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
N-Channel	30V	0.4Ω @ V _{GS} = 10V	0.8A
		0.7Ω @ V _{GS} = 4.5V	0.57A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

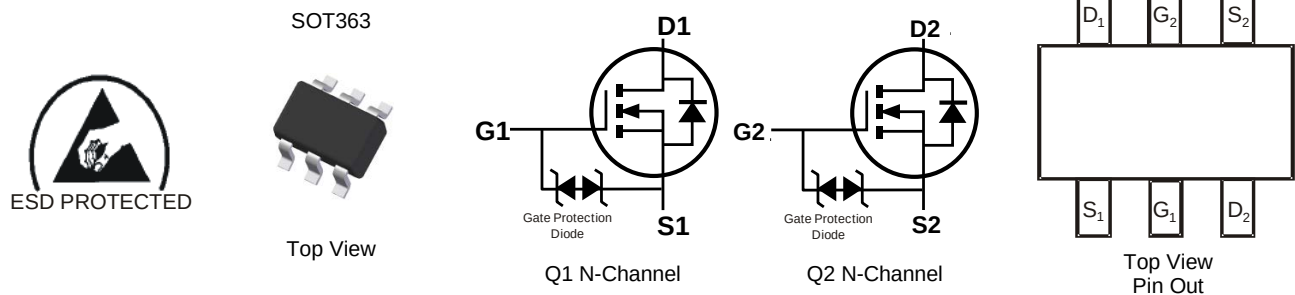
- Motor Control
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. "Green" Device (Note 3)**
- **The DMN3401LDWQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.**

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 
- Weight: 0.027 grams (Approximate)

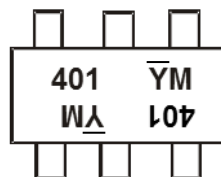


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3401LDWQ-7	SOT363	3000/Tape & Reel
DMN3401LDWQ-13	SOT363	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



401 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: H = 2020)
 M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027
Code	H	I	J	K	L	M	N	O

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DS}	30	V
Gate-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^{\circ}\text{C}$ $T_A = +70^{\circ}\text{C}$	I_D	0.8 0.6	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.4	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	4	A

Thermal Characteristics (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P_D	0.29	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		$R_{\theta JA}$	433	$^{\circ}\text{C/W}$
Total Power Dissipation (Note 6)			P_D	0.35	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	360	$^{\circ}\text{C/W}$
Operating and Storage Temperature Range			T_J, T_{STG}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.8	—	1.6	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.2	0.4	Ω	$V_{GS} = 10\text{V}, I_D = 0.59\text{A}$
		—	0.3	0.7		$V_{GS} = 4.5\text{V}, I_D = 0.2\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 10\text{mA}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	50	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	12	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	10	—	pF	
Gate Resistance	R_g	—	58	—	Ω	$V_{DS} = V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	0.5	—	nC	$V_{DS} = 10\text{V}, V_{GS} = 10\text{V}, I_D = 250\text{mA}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	1.2	—	nC	
Gate-Source Charge	Q_{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.1	—	nC	$V_{GS} = 10\text{V}, V_{DS} = 30\text{V}, I_D = 100\text{mA}, R_G = 25\Omega$
Turn-On Delay Time	$t_{D(ON)}$	—	3.5	—	ns	
Turn-On Rise Time	t_R	—	3.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	16.8	—	ns	
Turn-Off Fall Time	t_F	—	13.8	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

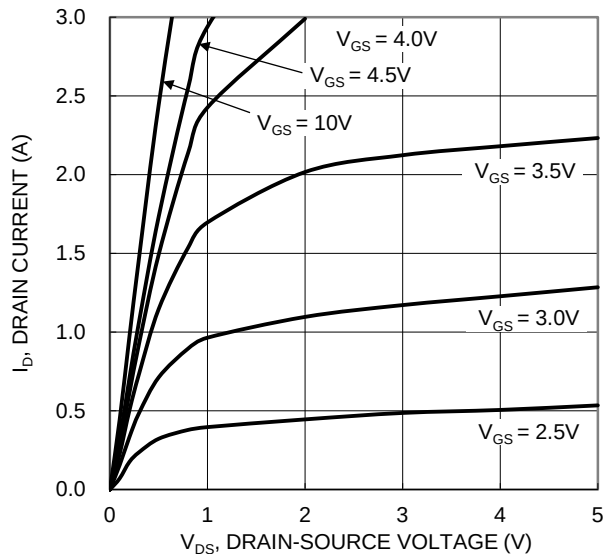


Figure 1. Typical Output Characteristic

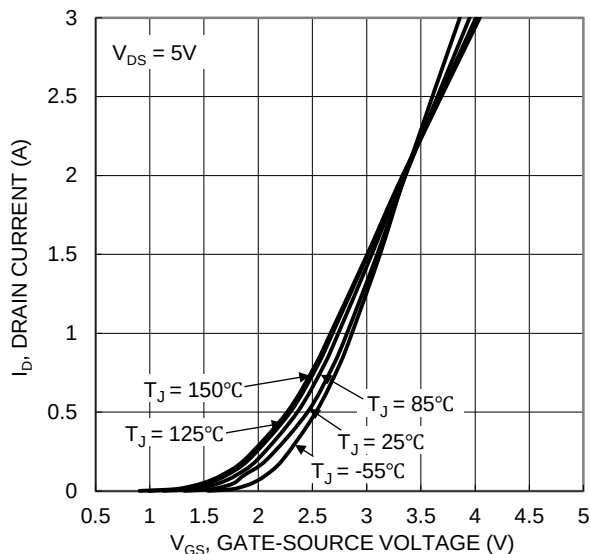


Figure 2. Typical Transfer Characteristic

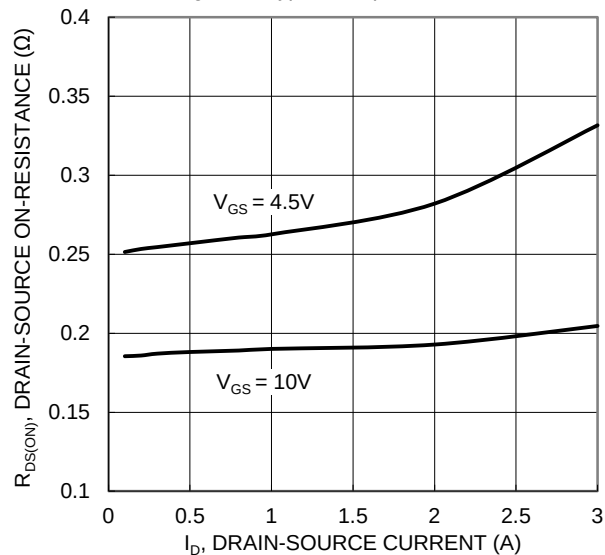


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

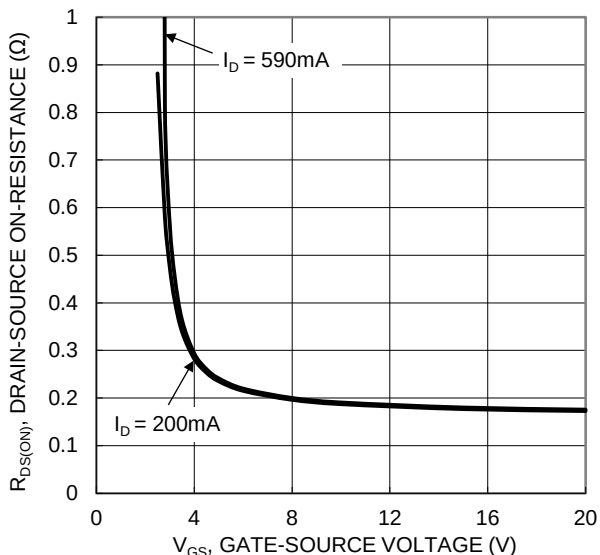


Figure 4. Typical Transfer Characteristic

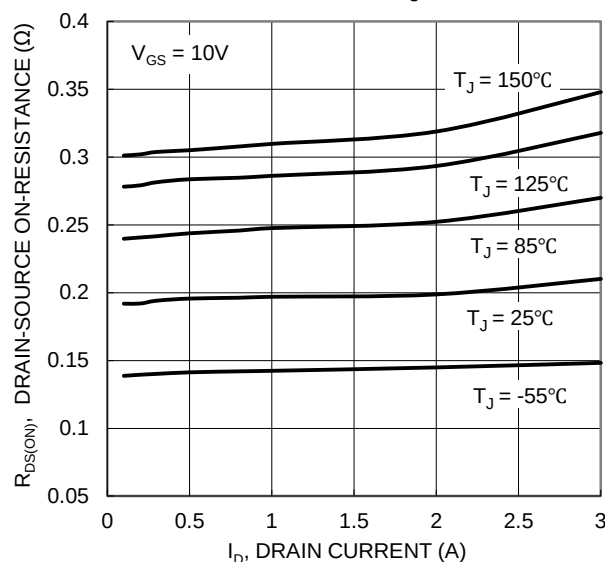


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

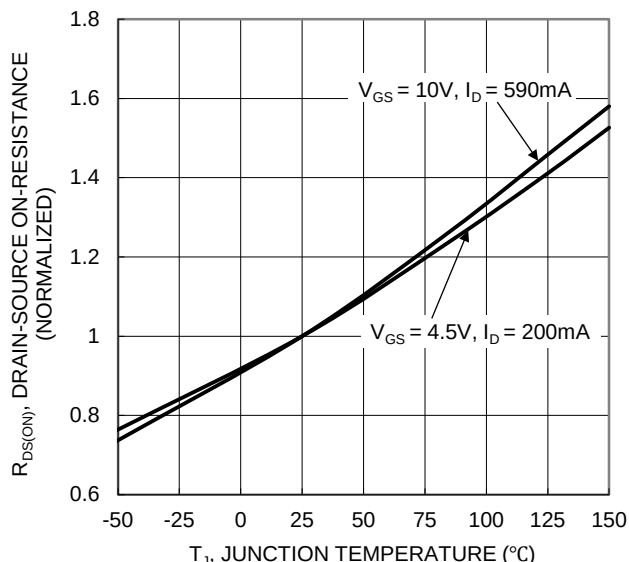
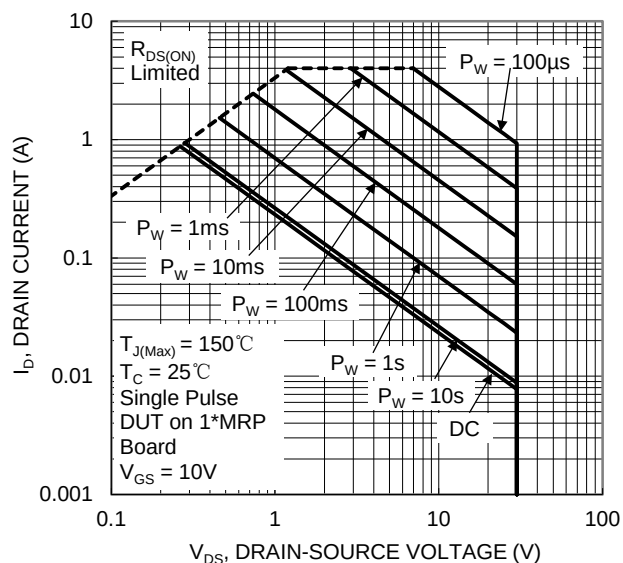
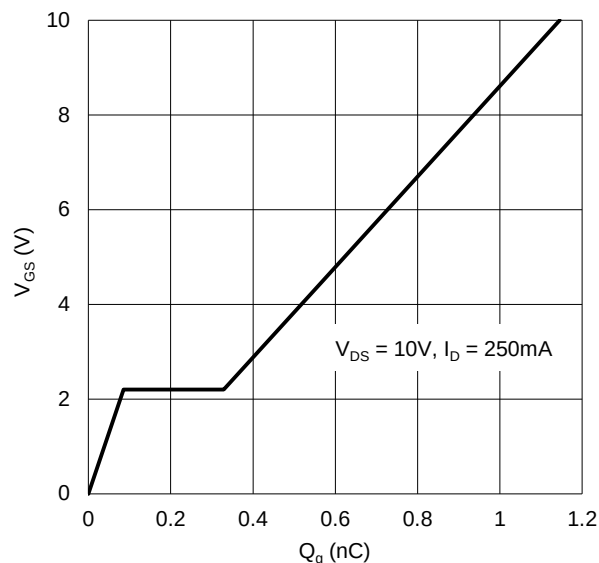
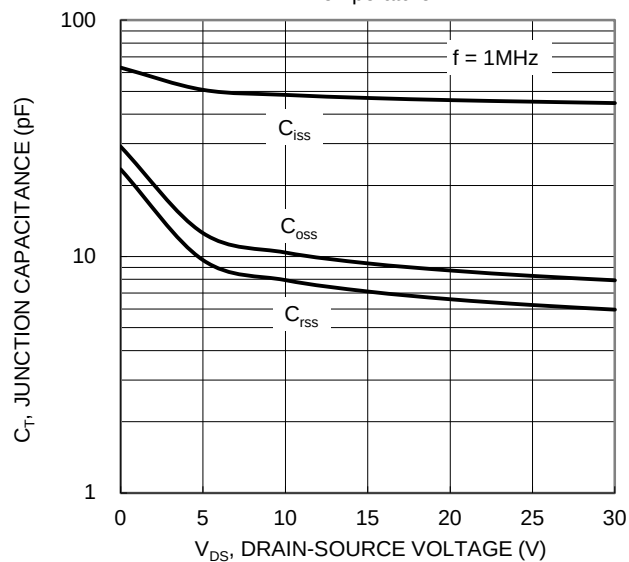
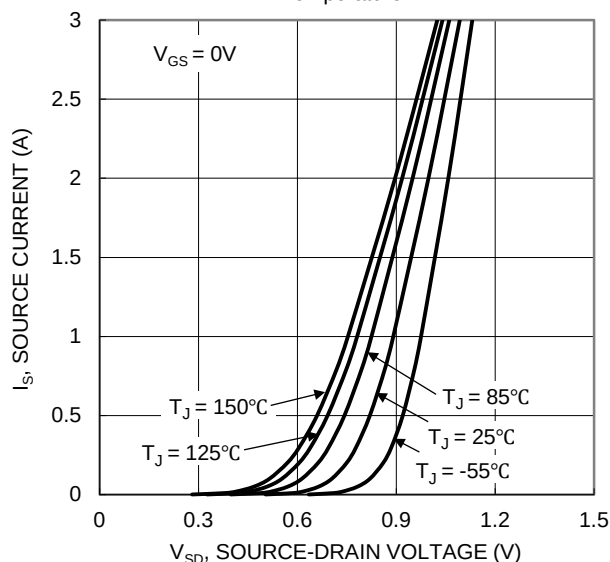
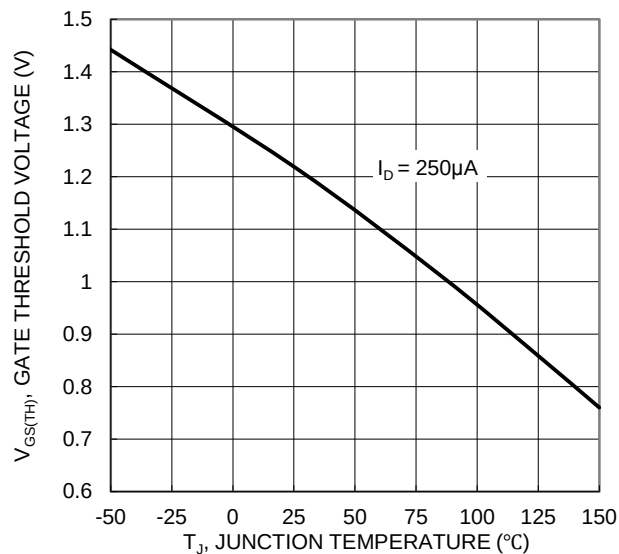
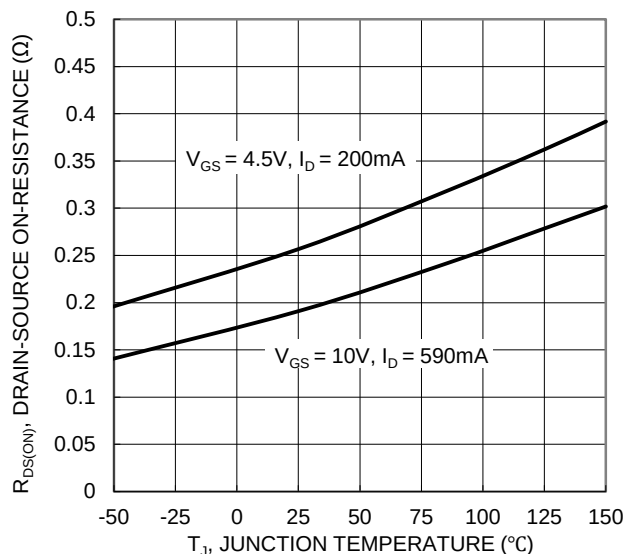


Figure 6. On-Resistance Variation with Junction Temperature



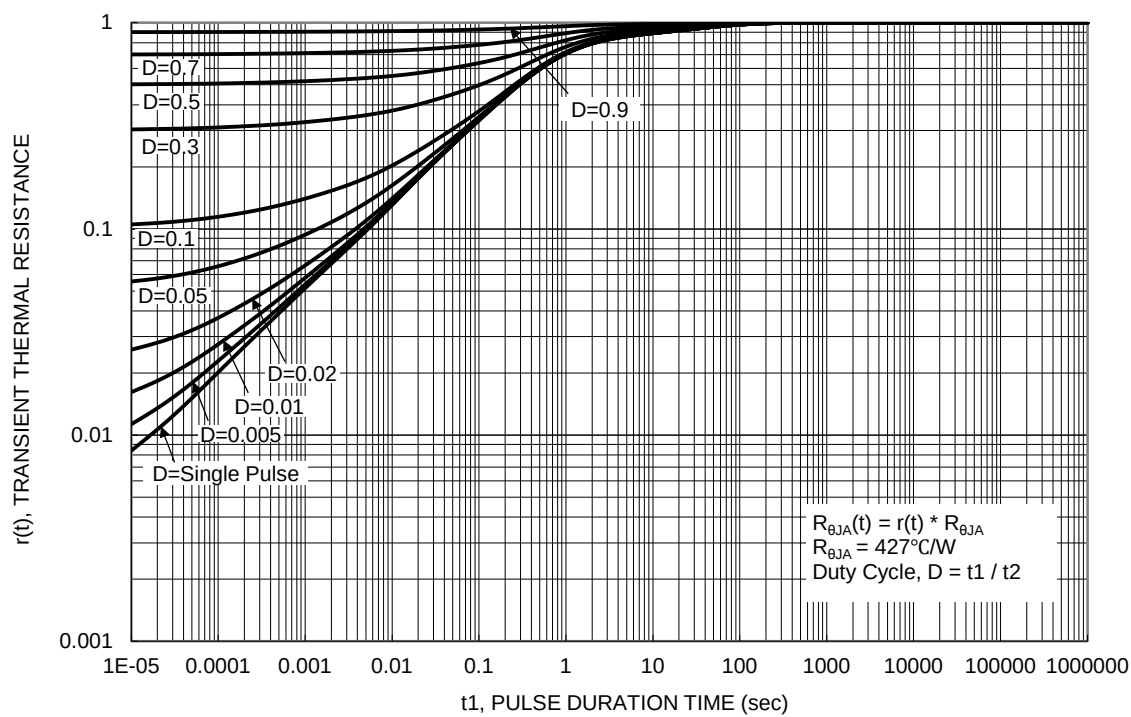
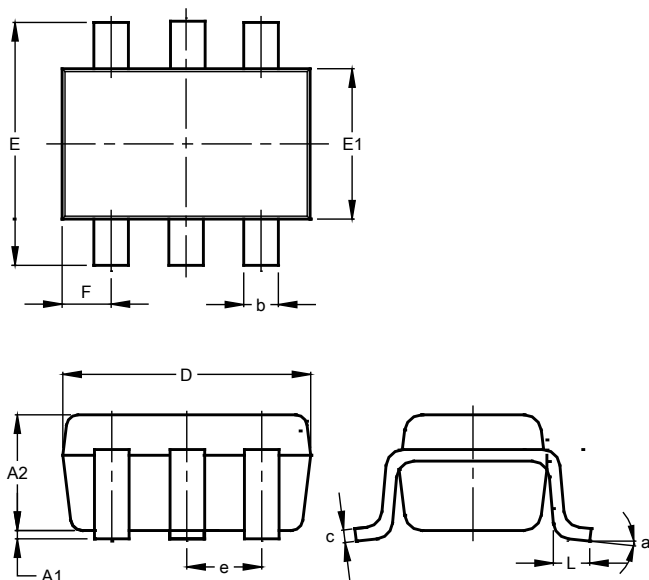


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

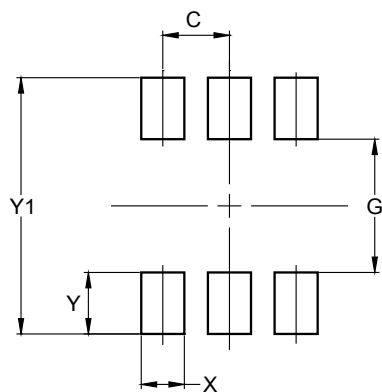
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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